

**TC74HC4066AP, TC74HC4066AF, TC74HC4066AFN, TC74HC4066AFT**

**QUAD BILATERAL SWITCH**

The TC74HC4066A is a high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C<sup>2</sup>MOS technology.

It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation.

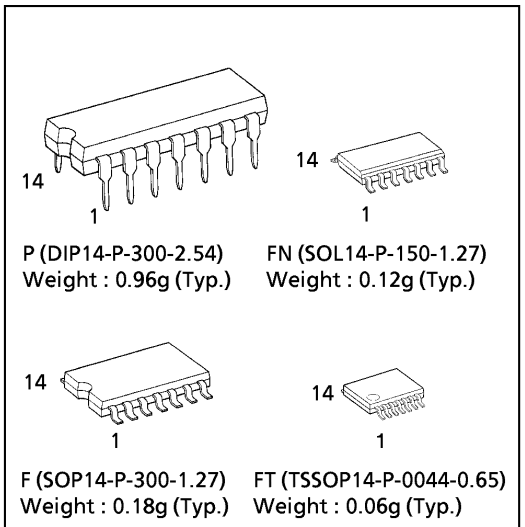
Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

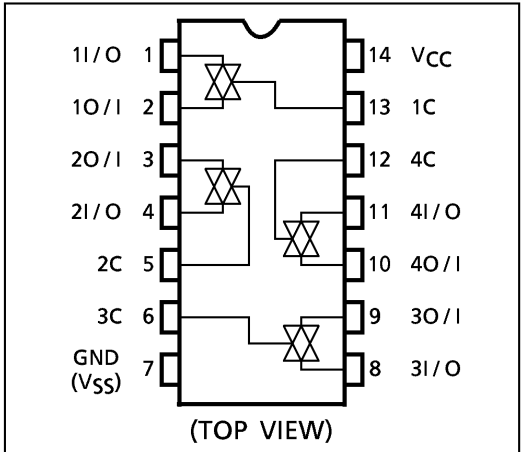
**FEATURES :**

- High Speed .....  $t_{pd} = 7\text{ns}(\text{typ.})$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation .....  $I_{CC} = 1\mu\text{A}(\text{Max.})$  at  $T_a = 25^\circ\text{C}$
- High Noise Immunity .....  $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Low ON Resistance .....  $R_{ON} = 50\Omega(\text{typ.})$  at  $V_{CC} = 9\text{V}$
- High Degree of Linearity .....  $\text{THD} = 0.05\%(\text{typ.})$  at  $V_{CC} = 5\text{V}$
- Pin and Function Compatible with 4066B

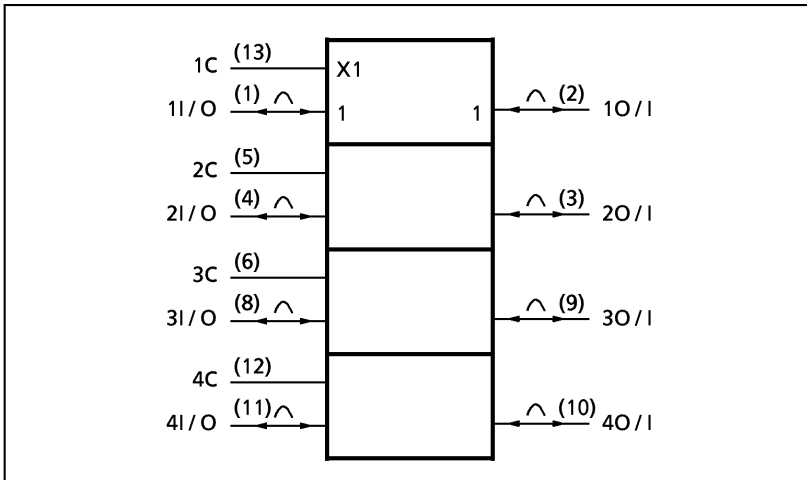
(Note) The JEDEC SOP (FN) is not available in Japan.



**PIN ASSIGNMENT**



**IEC LOGIC SYMBOL**



**TRUTH TABLE**

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~13	V
Control Input Voltage	$V_{IN}$	-0.5~ $V_{CC} + 0.5$	V
Switch I/O Voltage	$V_{I/O}$	-0.5~ $V_{CC} + 0.5$	V
Control Input Diode Current	$I_{IK}$	±20	mA
I/O Diode Current	$I_{OK}$	±20	mA
Switch through Current	$I_{OUT}$	±25	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	±50	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP / TSSOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}C \sim 65^{\circ}C$ . From  $T_a = 65^{\circ}C$  to  $85^{\circ}C$  a derating factor of  $-10mW/^{\circ}C$  shall be applied until 300mW.

**RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2~12	V
Control Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Switch I/O Voltage	$V_{I/O}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$t_r, t_f$	0~1000 ( $V_{CC} = 2.0V$ ) 0~500 ( $V_{CC} = 4.5V$ ) 0~400 ( $V_{CC} = 6.0V$ ) 0~250 ( $V_{CC} = 10.0V$ )	ns

**DC ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^{\circ}C$			$T_a = -40 \sim 85^{\circ}C$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Control Input Voltage	$V_{IHC}$		2.0	1.50	—	—	1.50	—	V
			4.5	3.15	—	—	3.15	—	
			9.0	6.30	—	—	6.30	—	
			12.0	8.40	—	—	8.40	—	
Low - Level Control Input Voltage	$V_{ILC}$		2.0	—	—	0.50	—	0.50	V
			4.5	—	—	1.35	—	1.35	
			9.0	—	—	2.70	—	2.70	
			12.0	—	—	3.60	—	3.60	
ON Resistance	$R_{ON}$	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $I_{I/O} \leq 1mA$	4.5	—	96	170	—	200	Ω
			9.0	—	55	85	—	100	
			12.0	—	45	80	—	90	
			2.0	—	160	—	—	—	
		$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ or GND $I_{I/O} \leq 1mA$	4.5	—	70	100	—	130	
			9.0	—	50	75	—	95	
			12.0	—	45	70	—	90	
			Difference of ON Resistance Between Switches	$\Delta R_{ON}$	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ to GND $I_{I/O} \leq 1mA$	4.5	—	10	
9.0	—	5				—	—	—	
12.0	—	5				—	—	—	
Input/Output Leakage Current (SWITCH OFF)	$I_{OFF}$	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ or $V_{CC}$ $V_{IN} = V_{ILC}$	12.0	—	—	±100	—	±1000	nA
Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	$I_{IZ}$	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{IHC}$	12.0	—	—	±100	—	±1000	
Control Input Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	12.0	—	—	±100	—	±1000	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA
			9.0	—	—	4.0	—	40.0	
			12.0	—	—	8.0	—	80.0	

**AC ELECTRICAL CHARACTERISTICS ( C<sub>L</sub> = 50pF, Input t<sub>r</sub> = t<sub>f</sub> = 6ns )**

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C			Ta = -40~85°C		UNIT	
			V <sub>CC</sub> (V)	MIN.	TYP.	MAX.	MIN.		MAX.
Phase difference between Input and Output	φ I-O		2.0	—	10	50	—	65	pF
			4.5	—	4	10	—	13	
			9.0	—	3	8	—	10	
			12.0	—	3	7	—	9	
Output Enable Time	t <sub>pZL</sub> t <sub>pZH</sub>	R <sub>L</sub> = 1KΩ	2.0	—	18	100	—	125	pF
			4.5	—	8	20	—	25	
			9.0	—	6	12	—	22	
			12.0	—	6	12	—	18	
Output Disable Time	t <sub>pLZ</sub> t <sub>pHZ</sub>	R <sub>L</sub> = 1KΩ	2.0	—	20	115	—	145	pF
			4.5	—	10	23	—	29	
			9.0	—	8	20	—	25	
			12.0	—	8	18	—	22	
Maximum Control Input Frequency		R <sub>L</sub> = 1KΩ C <sub>L</sub> = 15pF V <sub>OUT</sub> = 1/2 V <sub>CC</sub>	2.0	—	30	—	—	—	MHz
			4.5	—	30	—	—	—	
			9.0	—	30	—	—	—	
			12.0	—	30	—	—	—	
Control Input Capacitance	C <sub>IN</sub>		—	5	10	—	10	pF	
Switch Terminal Capacitance	C <sub>I/O</sub>		—	6	—	—	—		
Feed through Capacitance	C <sub>IOS</sub>		—	0.5	—	—	—		
Power Dissipation Capacitance	C <sub>PD</sub>	Note (1)	—	15	—	—	—		

Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC} (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \text{ (per channel)}$$

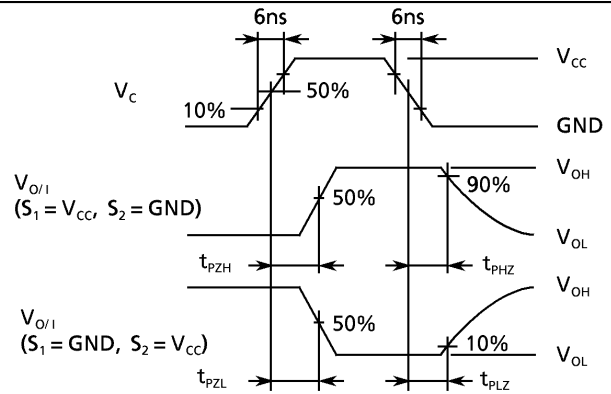
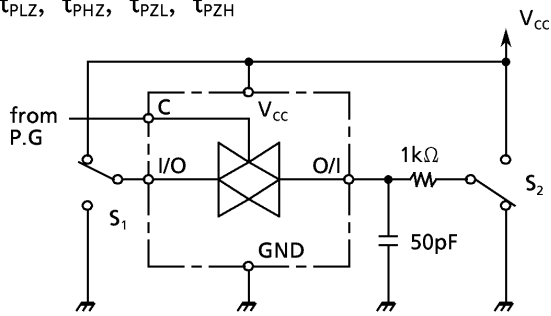
**ANALOG SWITCH CHARACTERISTICS ( GND = 0V, Ta = 25°C )**

PARAMETER	SYMBOL	TEST CONDITION	V <sub>CC</sub> (V)	TYP.	UNIT
Sine Wave Distortion (T. H. D)		f <sub>IN</sub> = 1kHz R <sub>L</sub> = 10kΩ C <sub>L</sub> = 50pF V <sub>IN</sub> = 4.0V <sub>P-P</sub> V <sub>IN</sub> = 8.0V <sub>P-P</sub> @V <sub>CC</sub> = 4.5V @V <sub>CC</sub> = 9.0V	4.5 9.0	0.05 0.04	%
Frequency Response (Switch ON)	f <sub>MAX</sub>	Adjust f <sub>IN</sub> voltage to obtain 0dBm at V <sub>OS</sub> Increase f <sub>IN</sub> Frequency until dB Meter reads -3dB R <sub>L</sub> = 50Ω, C <sub>L</sub> = 10pF f <sub>IN</sub> = 1MHz, Sine Wave	4.5 9.0	200 200	MHz
Feedthrough Attenuation (Switch OFF)		V <sub>in</sub> is centered at V <sub>CC</sub> /2 Adjust input for 0dBm R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF f <sub>IN</sub> = 1MHz, Sine Wave	4.5 9.0	-60 -60	dB
Crosstalk (Control Input to Signal Output)		R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF f <sub>IN</sub> = 1MHz, Square Wave (t <sub>r</sub> = t <sub>f</sub> = 6ns)	4.5 9.0	60 100	mV
Crosstalk (Between any switches)		Adjust V <sub>IN</sub> to obtain 0dBm at Input R <sub>L</sub> = 600Ω, C <sub>L</sub> = 50pF f <sub>IN</sub> = 1MHz, Sine Wave	4.5 9.0	-60 -60	dB

Note : These characteristics are determined by design of devices.

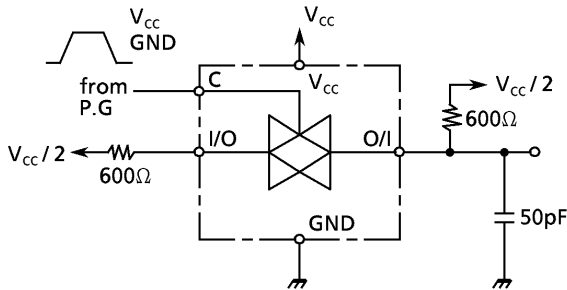
SWITCHING CHARACTERISTICS TEST CIRCUITS

1.  $t_{PLZ}$ ,  $t_{PHZ}$ ,  $t_{PZL}$ ,  $t_{PZH}$

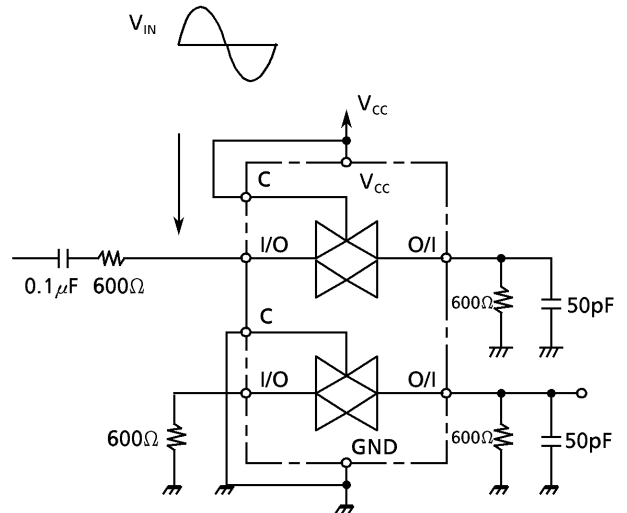


2. CROSS TALK (CONTROL INPUT-SWITCH OUTPUT)

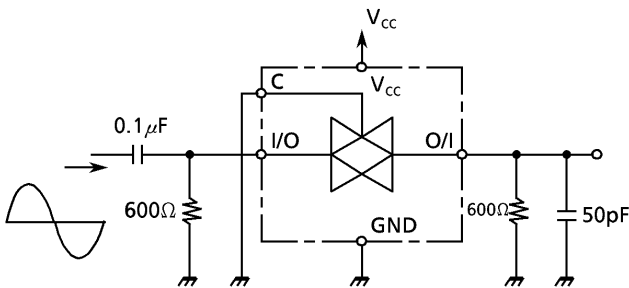
$f_{in} = 1\text{MHz}$   $\text{duty} = 50\%$   $t_r = t_f = 6\text{ns}$



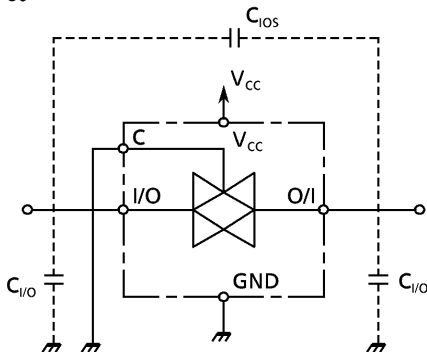
5. CROSSTALK (BETWEEN ANY TWO SWITCHES)



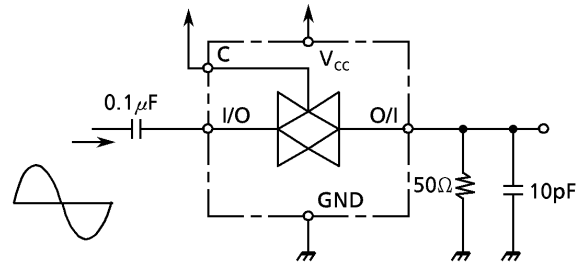
3. FEEDTHROUGH ATTENUATION



4.  $C_{IOS}$ ,  $C_{IS}$ ,  $C_{OS}$

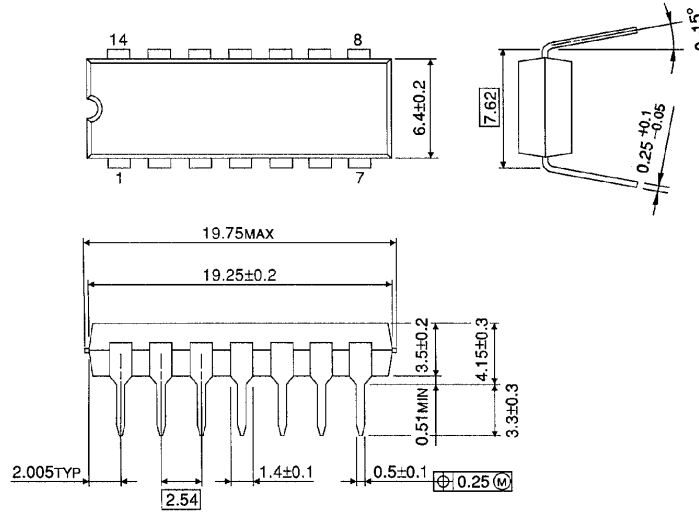


6. FREQUENCY RESPONSE (SWITCH ON)



**DIP 14PIN PACKAGE DIMENSIONS (DIP14-P-300-2.54)**

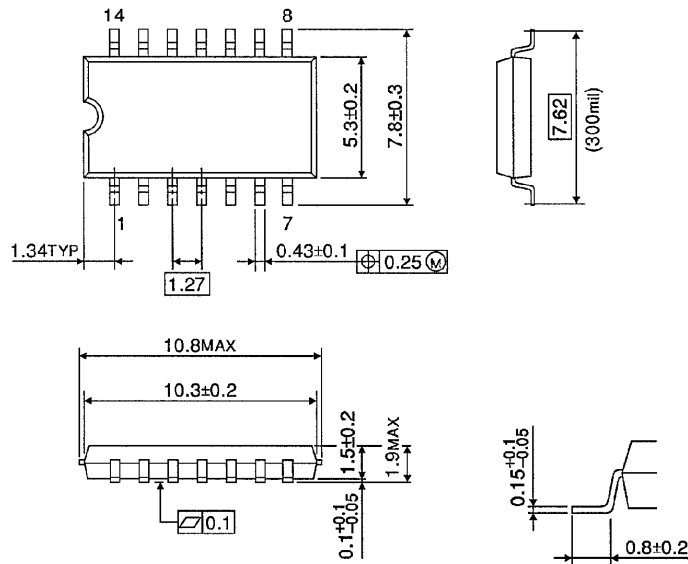
Unit in mm



Weight : 0.96g (Typ.)

**SOP 14PIN (200mil BODY) PACKAGE DIMENSIONS (SOP14-P-300-1.27)**

Unit in mm

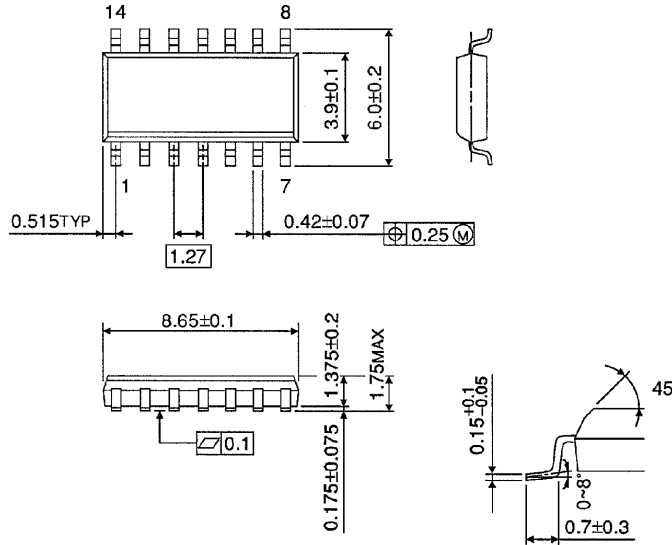


Weight : 0.18g (Typ.)

**SOP 14PIN (150mil BODY) PACKAGE DIMENSIONS (SOL14-P-150 -1.27)**

Unit in mm

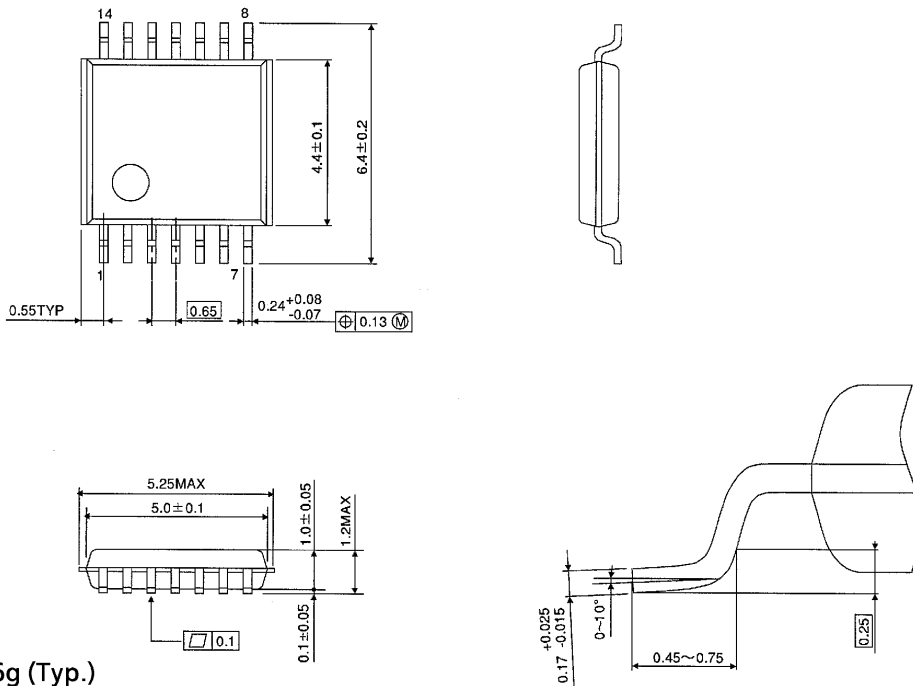
(Note) This package is not available in Japan.



Weight : 0.12g (Typ.)

**TSSOP 14PIN (170mil BODY) PACKAGE DIMENSIONS (TSSOP14-P-0044-0.65)**

Unit in mm



Weight : 0.06g (Typ.)

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